

## Claim Amendments

Please amend the claims as follows.

Claims 1-16 (canceled)

17. (original) A surface acoustic wave (SAW) device sealed at the wafer level, the device comprising:
  - an active area to be protected;
  - an electrical contact area; and
  - a lithographically-formed structure sealing at least the active area and leaving at least a portion of the electrical contact area exposed.
18. (original) The device of claim 17, wherein the lithographically-formed structure comprises a glassy material.
19. (original) The device of claim 17, wherein the SAW device is fabricated on a substrate from a group of substrates consisting of lithium tantalate, lithium niobate, and quartz.
20. (original) A lithographically-fabricated surface acoustic wave (SAW) device, the SAW device comprising:
  - means for carrying a surface acoustic wave; and
  - a wafer-level means for sealing the means for carrying the surface acoustic wave.
21. (new) The SAW device of claim 20, wherein the means for carrying the surface acoustic wave comprises a transducer structure.
22. (new) The SAW device of claim 21, wherein the transducer structure comprises aluminum patterned into interdigitated electrode fingers.

- 23. (new) The SAW device of claim 20, wherein the wafer-level means for sealing comprises a lithographically-formed structure sealing at least the means for carrying.
- 24. (new) The SAW device of claim 23, further comprising electrical contact areas coupled to the means for carrying, and wherein the wafer-level means for sealing leaves exposed at least a portion of the electrical contact areas.
- 25. (new) The device of claim 17, wherein the lithographically-formed structure comprises a material of a thickness so as to be impermeable to undesired contaminants.
- 26. (new) The device of claim 17, wherein the lithographically-formed structure comprises silicon dioxide.
- 27. (new) The device of claim 17, wherein the lithographically-formed structure comprises silicon nitride.
- 28. (new) The device of claim 17, wherein the lithographically-formed structure comprises a metal.
- 29. (new) The device of claim 18, wherein the glassy material comprises a spin-on-glass.
- 30. (new) The device of claim 18, wherein the glassy material comprises a sputtered glass.
- 31. (new) The device of claim 17, wherein the SAW device is fabricated on a lithium tantalate substrate.
- 32. (new) The device of claim 17, wherein the SAW device is fabricated on a lithium niobate substrate.

33. (new) The device of claim 17, wherein the SAW device is fabricated on a quartz substrate.